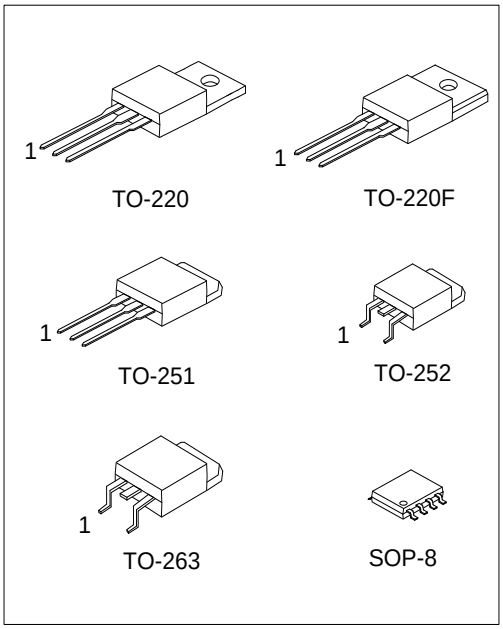
UTT36N10

Power MOSFET

36A, 100V N-CHANNEL POWER MOSFET



■ DESCRIPTION

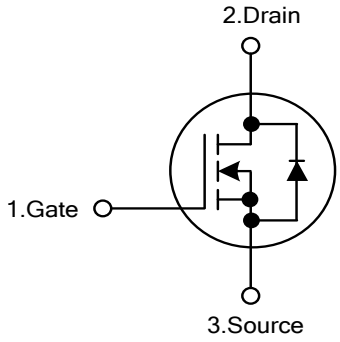
The UTC **UTT36N10** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, low gate charge and high switching speed.

The UTC **UTT36N10** is suitable for high voltage synchronous rectifier and DC/DC converters, etc.

■ FEATURES

* High Switching Speed

■ SYMBOL



■ ORDERING INFORMATION

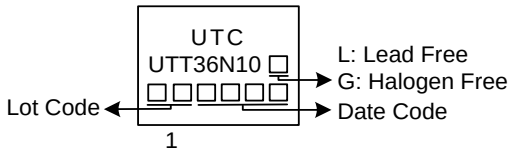
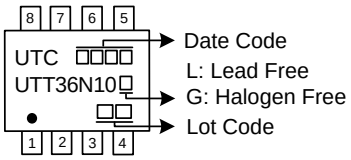
Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UTT36N10L-TA3-T	UTT36N10G-TA3-T	TO-220	G	D	S	-	-	-	-	-	Tube
UTT36N10L-TF3-T	UTT36N10G-TF3-T	TO-220F	G	D	S						Tube
UTT36N10L-TM3-T	UTT36N10G-TM3-T	TO-251	G	D	S						Tube
UTT36N10L-TN3-R	UTT36N10G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
UTT36N10L-TQ2-T	UTT36N10G-TQ2-T	TO-263	G	D	S	-	-	-	-	-	Tube
UTT36N10L-TQ2-R	UTT36N10G-TQ2-R	TO-263	G	D	S	-	-	-	-	-	Tape Reel
UTT36N10L-S08-R	UTT36N10G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UTT36N10G-TA3-T
- (1)Packing Type
- (2)Package Type
- (3)Green Package

(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF3: TO-220F, TM3: TO-251
TN3: TO-252, TQ2: TO-263, S08: SOP-8
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING

TO-220 / TO-220F / TO-251 / TO-252 / TO-263	SOP-8
	

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous (V_{GS}=10V) T_C=25°C	I_D	36	A
	Pulsed	I_{DM}	72	A
Single Pulsed Avalanche Energy		E_{AS}	33.8 (Note 3)	mJ
Power Dissipation	TO-220/TO-263	P_D	125	W
	TO-220F		36	W
	TO-251/TO-252		44	W
	SOP-8		6	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L=0.1mH, I_{AS}=26A, V_{DD}= 50V, R_G=25Ω, Starting T_J=25°C.
4. I_{SD} ≤30A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J=25°C.

■ THERMAL DATA

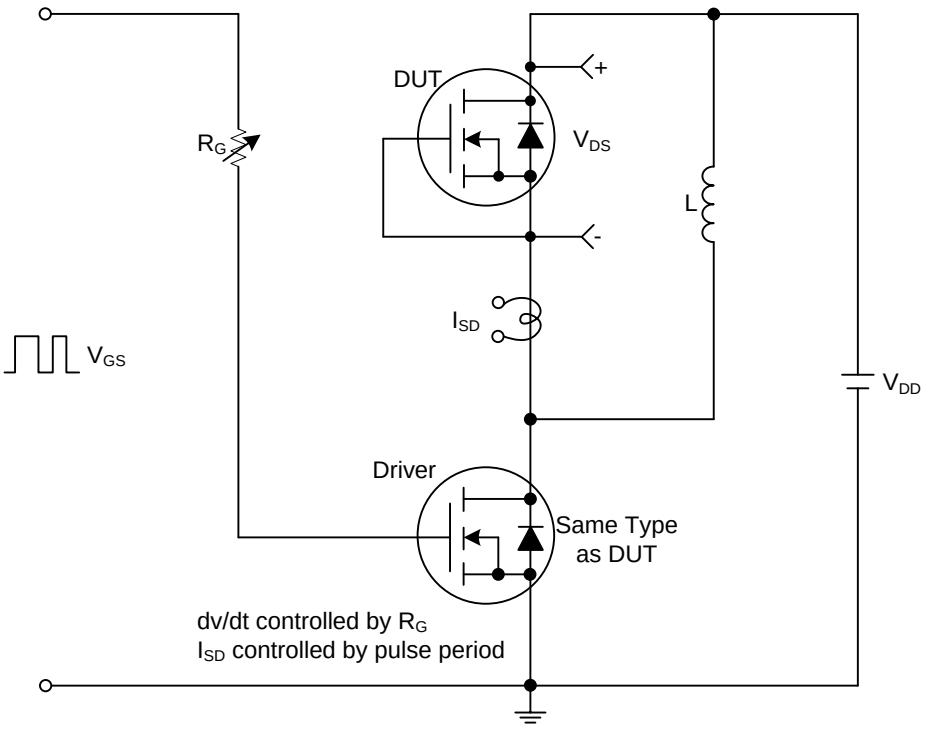
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-263	θ_{JA}	62.5	°C/W
	TO-251/TO-252		110	°C/W
	SOP-8		100	°C/W
Junction to Case	TO-220/TO-263	θ_{JC}	1	°C/W
	TO-220F		3.47	°C/W
	TO-251/TO-252		2.85 (Note)	°C/W
	SOP-8		20.8 (Note)	°C/W

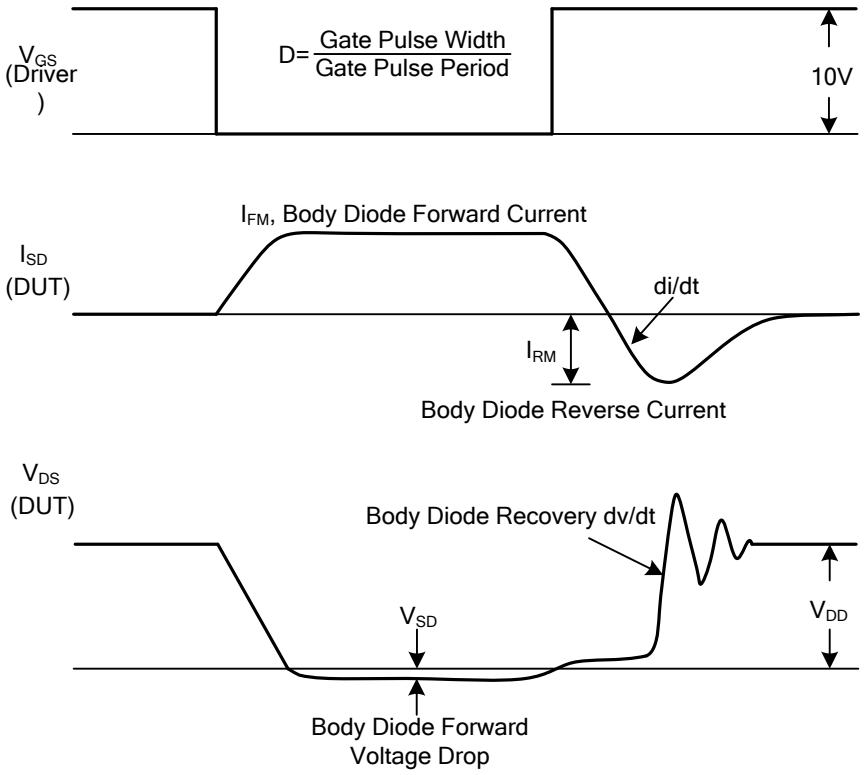
Note: The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	100			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=100V, V_{GS}=0V			1	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	1.0		3.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=30A			44	mΩ
			V_{GS}=4.5V, I_D=15A			48	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		2950		pF
Output Capacitance		C_{OSS}			152		pF
Reverse Transfer Capacitance		C_{RSS}			124		pF
SWITCHING PARAMETERS							
Total Gate Charge at 10V		Q_G	V_{DD}=80V, I_D=36A, V_{GS}=10V, I_G=1mA		63		nC
Gate to Source Charge		Q_{GS}			7		nC
Gate to Drain Charge		Q_{GD}			14		nC
Turn-ON Time		t_{ON}	V_{DD}=50V, I_D=36A, V_{GS}=10V, R_G=3Ω		10		ns
Turn-ON Delay Time		$t_{D(ON)}$			18		ns
Rise Time		t_R			46		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			20		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V_{SD}	I_{SD}=36A			1.4	V

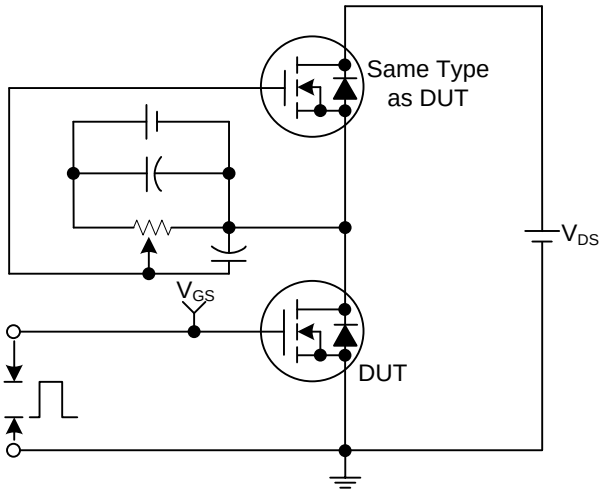
■ TEST CIRCUITS AND WAVEFORMS



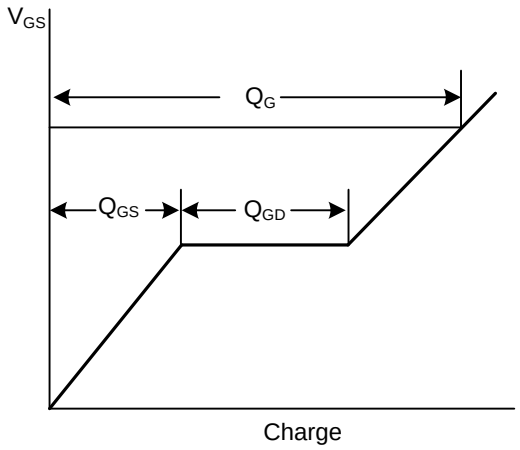


Peak Diode Recovery dv/dt Test Circuit and Waveforms

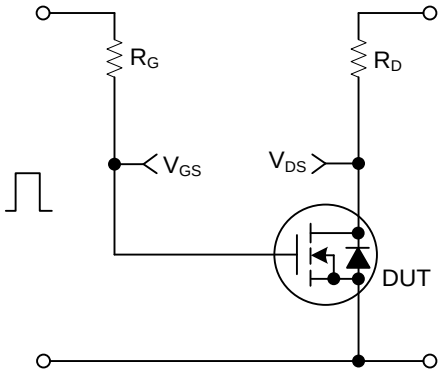
■ TEST CIRCUITS AND WAVEFORMS



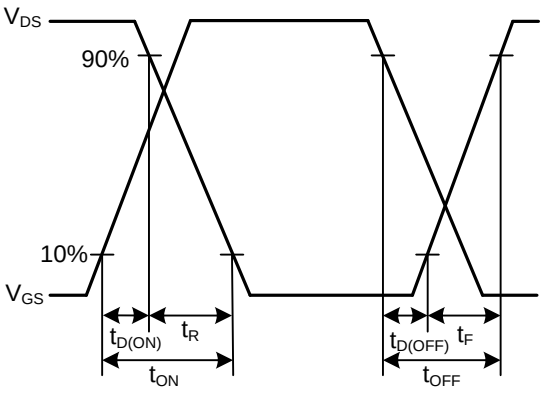
Gate Charge Test Circuit



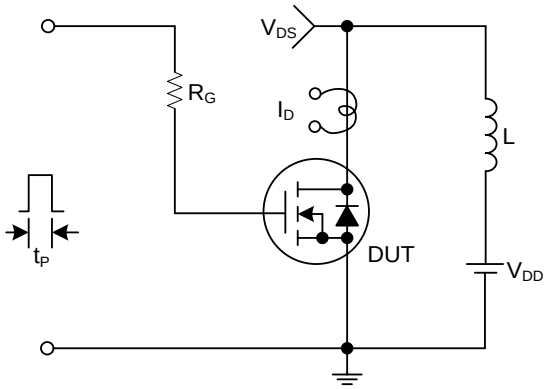
Gate Charge Waveforms



Resistive Switching Test Circuit

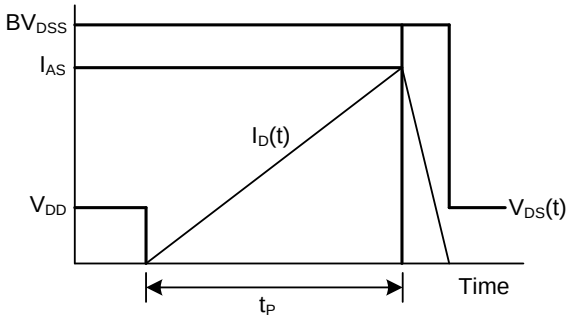


Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit

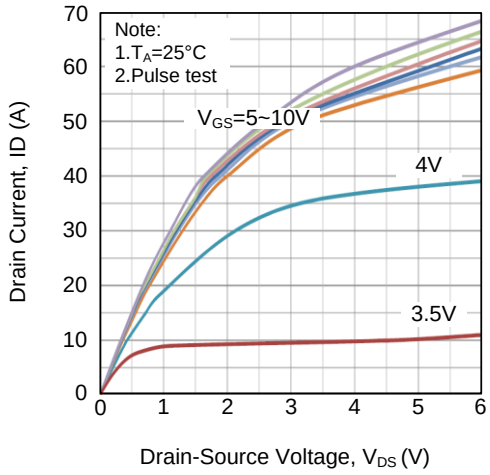
$$E_{AS}=\frac{1}{2}LI_{AS}^{2}\frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$



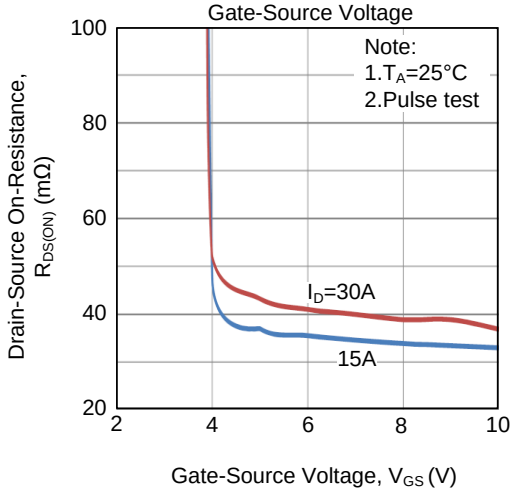
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

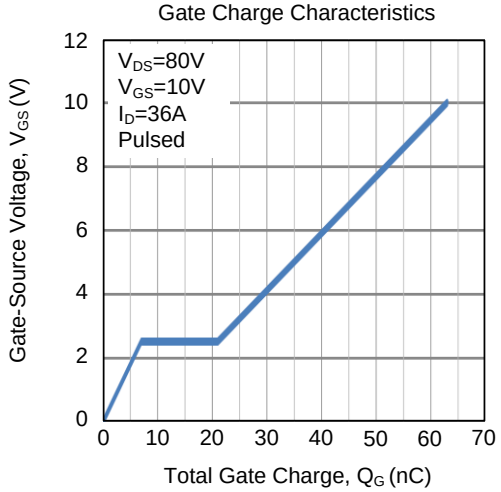
Drain Current vs. Drain-Source Voltage



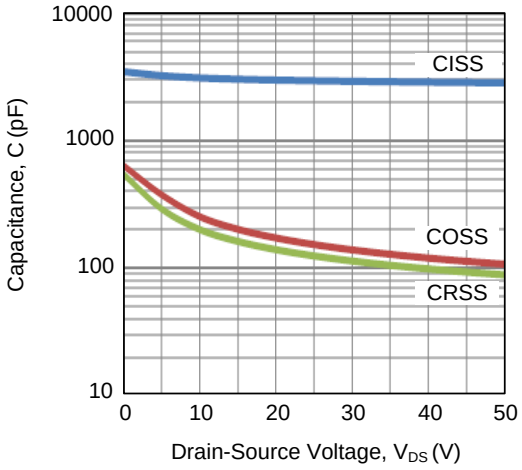
Drain-Source On-Resistance vs. Gate-Source Voltage



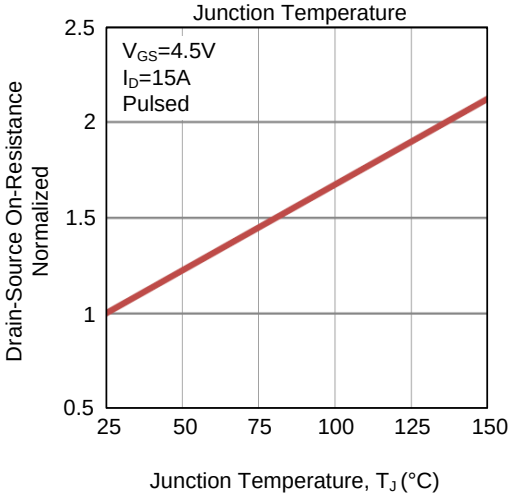
Gate Charge Characteristics



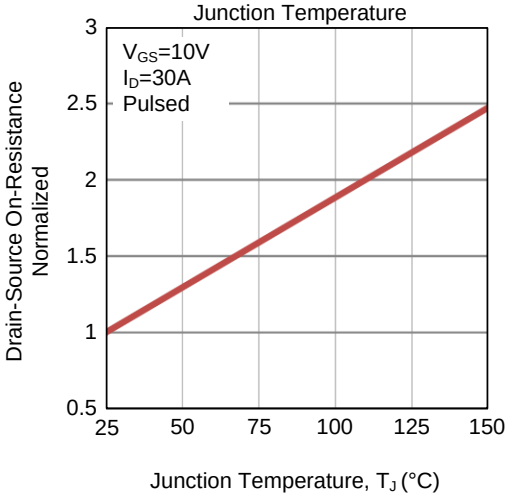
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

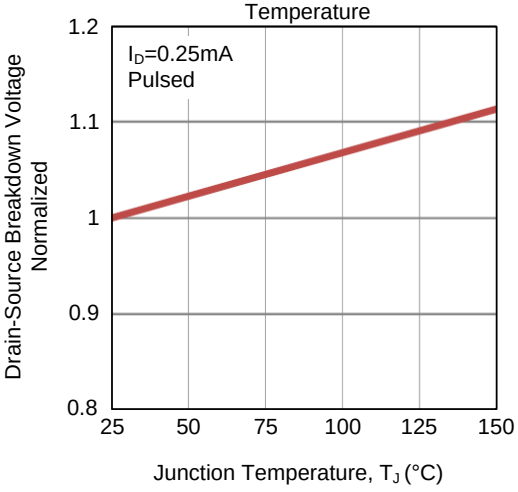


Drain-Source On-Resistance vs. Junction Temperature

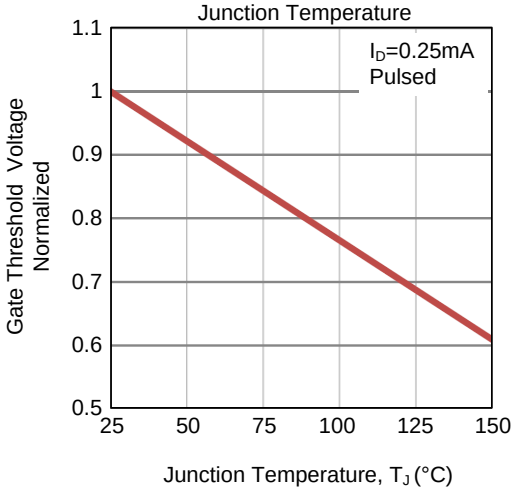


■ TYPICAL CHARACTERISTICS (Cont.)

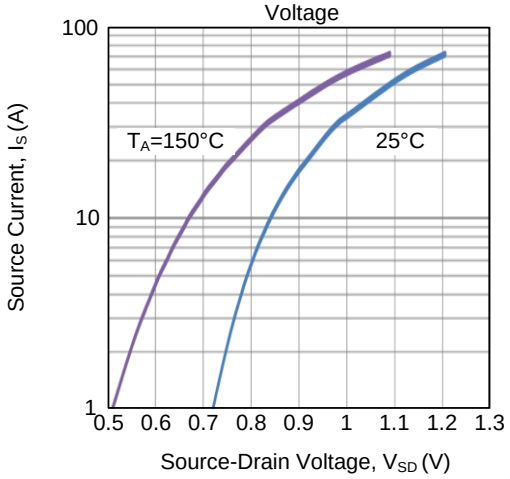
Breakdown Voltage vs. Junction Temperature



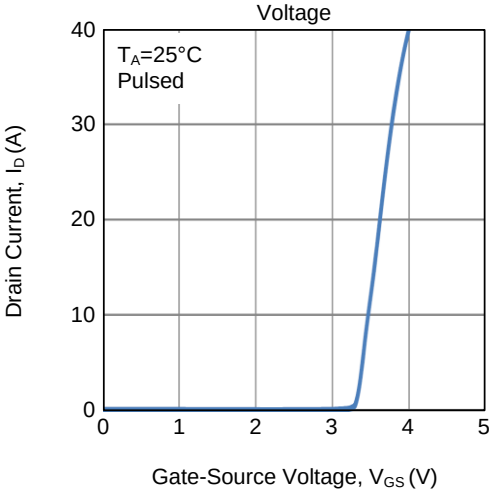
Gate Threshold Voltage vs. Junction Temperature



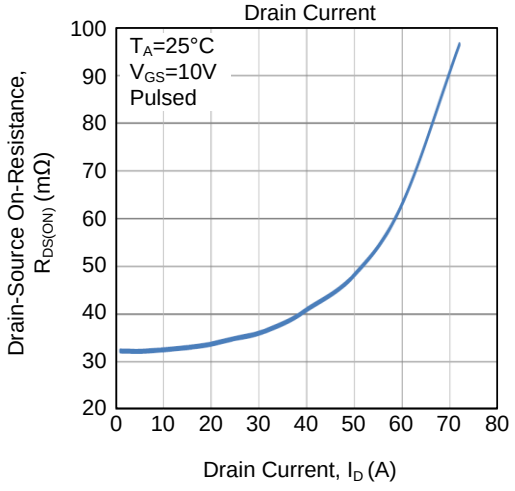
Source Current vs. Source-Drain Voltage



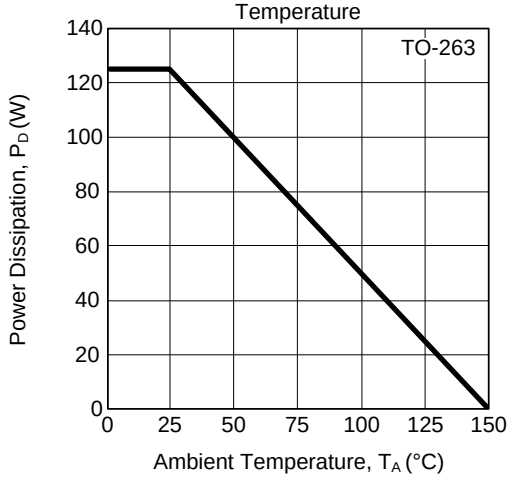
Drain Current vs. Gate-Source Voltage



Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Ambient Temperature



■ TYPICAL CHARACTERISTICS (Cont.)